

ABSTRACT OF THE DISCLOSURE

A semiconductor device includes at least one thin film transistor including a semiconductor layer that has a crystalline region including a channel region, a source region and a drain region, a gate insulating film disposed at least on the channel region, the source region and the drain region of the semiconductor layer, and a gate electrode arranged so as to oppose the channel region via the gate insulating film. At least a portion of the semiconductor layer includes a catalyst element capable of promoting crystallization, and the semiconductor layer further includes a gettering region that includes the catalyst element at a higher concentration than in the channel region or the source region and the drain region. The thickness of the gate insulating film on the gettering region is smaller than that on the source region and the drain region, or the gate insulating film is not disposed on the gettering region.